1 A very low V_F MEGA Schottky barrier rectifiers

Rev. 03 — 28 March 2007

Pro

Product data sheet

Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview**

Type number	Package		Configuration	
	NXP	JEITA		
PMEG2010AEH	SOD123F	-	single	
PMEG2010AET	SOT23	-	single	

1.2 Features

Forward current: I_F ≤ 1 A

Reverse voltage: V_R ≤ 20 V

Very low forward voltage

Small SMD plastic packages

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 2. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{F}	forward current	$T_{sp} \le 55 ^{\circ}C$	-	-	1	Α
V_R	reverse voltage		-	-	20	V
V _F	forward voltage	I _F = 1 A	<u>[1]</u> _	380	430	mV

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.



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2. Pinning information

Table 3. Pinning

Table 3.	rinning		
Pin	Description	Simplified outline	Symbol
SOD123F			
1	cathode	[1]	
2	anode	1 2	1 - 2
			sym001
SOT23			
1	anode		_
2	not connected	3	3
3	cathode	1 2	1

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PMEG2010AEH	-	plastic surface-mounted package; 2 leads	SOD123F
PMEG2010AET	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PMEG2010AEH	AF
PMEG2010AET	*AX

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

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5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{R}	reverse voltage		-	20	V
I _F	forward current	$T_{sp} \le 55 ^{\circ}C$	-	1	Α
I _{FRM}	repetitive peak forward current	$\begin{array}{l} t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25 \end{array}$			
	PMEG2010AEH		-	7	Α
	PMEG2010AET		-	6	Α
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	-	9	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PMEG2010AEH		<u>[1]</u> -	375	mW
			[2] _	830	mW
	PMEG2010AET		[1] -	280	mW
			[2] _	420	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PMEG2010AEH		[2] _	-	330	K/W
			[3]	-	150	K/W
	PMEG2010AET		[2] _	-	440	K/W
			[3]	-	300	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[4]			
	PMEG2010AEH		-	-	60	K/W
	PMEG2010AET		-	-	120	K/W

^[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

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^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[4] Soldering point of cathode tab.

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7. Characteristics

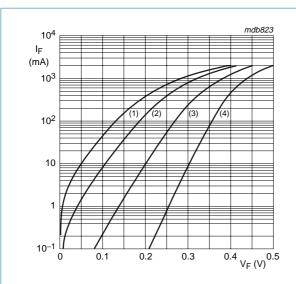
Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F forward voltage	forward voltage		<u>[1]</u>			
	I _F = 10 mA	-	200	220	mV	
		I _F = 100 mA	-	265	290	mV
		I _F = 1 A	-	380	430	mV
I _R reverse current	$V_R = 5 V$	-	15	50	μΑ	
		V _R = 10 V	-	20	80	μΑ
		V _R = 20 V	-	50	200	μΑ
C _d	diode capacitance	$V_R = 5 V$; $f = 1 MHz$	-	55	70	pF

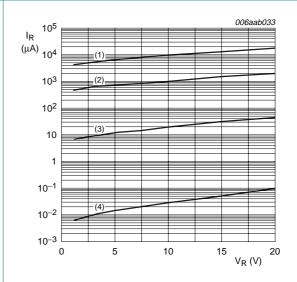
^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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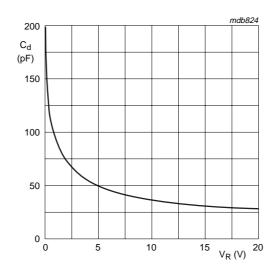
- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \,^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values

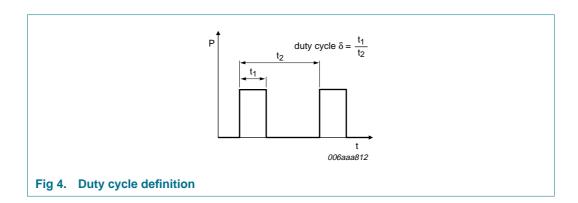


f = 1 MHz; T_{amb} = 25 °C

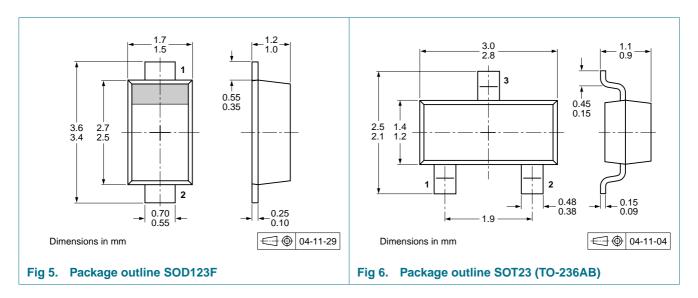
Fig 3. Diode capacitance as a function of reverse voltage; typical values

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8. Test information



9. Package outline



10. Packing information

Table 9. Packing methods

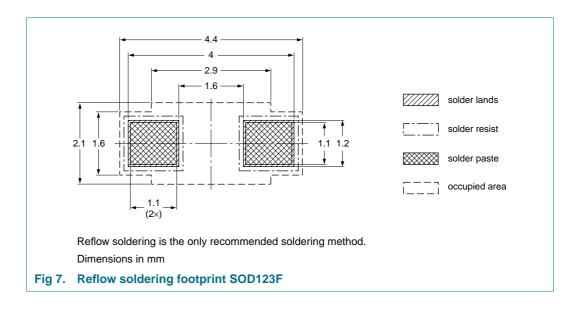
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description Packing q		quantity	
			3000	10000	
PMEG2010AEH	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135	
PMEG2010AET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	

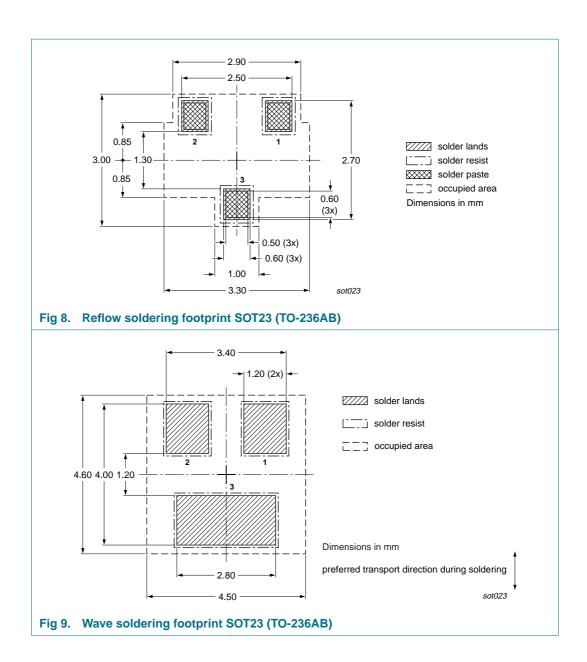
[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG2010AEH_PMEG2010AET_3	20070328	Product data sheet	-	PMEG2010AEH_2
Modifications:		f this data sheet has bee	•	ply with the new
	 Legal texts have 	ave been adapted to the	new company name	where appropriate.
	 Type number 	PMEG2010AET added		
	• Section 1.1 "	General description": am	ended	
	• Table 1 "Proc	duct overview": added		
	• Table 7 "Ther	rmal characteristics": Tat	ole note 1 amended	
	• Table 7 "Ther	rmal characteristics": Tat	ole note 4 added	
	• Table 8 "Cha	racteristics": C _d diode ca	pacitance conditions	adapted
	• Figure 2: ame	ended		
	 Section 8 "Te 	est information": added		
	 Section 13 "L 	<u>egal information"</u> : updat	ed	
PMEG2010AEH_2	20050526	Product data sheet	-	PMEG2010AEH_1
PMEG2010AEH_1	20050406	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PMEG2010AEH; PMEG2010AET

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